美浦森半导体
M s e m i t e k

Halogen Free

RoHS LEAD FREE

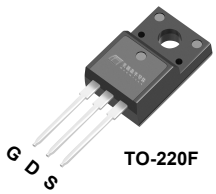
SLF9N90C / SLH9N90C
900V N-Channel MOSFET

General Description

This Power MOSFET is produced using Msemitek's advanced planar stripe DMOS technology.
This advanced technology has been especially tailored to minimize conduction loss, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.
These devices are well suited for AC/DC power conversion in switching mode operation for higher efficiency.

Features

- 9A, 900V, $R_{DS(on)\ typ.}$ = 975mΩ@V_{GS} = 10 V
- Low gate charge (typical 80nC)
- Low Crss (typical 36pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



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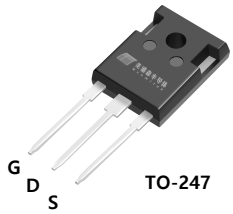

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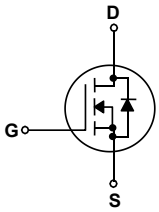

Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		SLF9N90C / SLH9N90C	Units
V_{DSS}	Drain-Source Voltage		900	V
I_D	Drain Current - Continuous (T_C = 25℃)		9	A
	- Continuous (T_C = 100℃)		5.8	A
I_{DM}	Drain Current - Pulsed	(Note 1)	36	A
V_{GSS}	Gate-Source Voltage		±30	V
EAS	Single Pulsed Avalanche Energy	(Note 2)	576	mJ
I_{AR}	Avalanche Current	(Note 1)	9	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	53	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5	V/ns
P_D	Power Dissipation (T_C = 25℃)		31.2	W
	- Derate above 25℃		0.25	W/℃
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	℃

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	SLF9N90C / SLH9N90C	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	4.0	℃/W
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	--	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	48	℃/W

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Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 uA	900	--	--	V
$\triangle BV_{DSS}$ / $\triangle T_J$	Breakdown Voltage Temperature Coefficient	I_D = 250 uA, Referenced to 25℃	--	0.74	--	V/℃
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 900 V, V_{GS} = 0 V	--	--	1	uA
		V_{DS} = 720 V, T_C = 125℃	--	--	10	uA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 uA	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 4.5 A	--	975	1200	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D = 4.5 A (Note 4)	--	11	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	2752	--	pF
C_{oss}	Output Capacitance		--	206	--	pF
C_{rss}	Reverse Transfer Capacitance		--	36	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 450 V, I_D = 9.0 A, R_G = 25 Ω (Note 4, 5)	--	33	--	ns
t_r	Turn-On Rise Time		--	57	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	270	--	ns
t_f	Turn-Off Fall Time		--	91	--	ns
Q_g	Total Gate Charge	V_{DS} = 720 V, I_D = 9.0 A, V_{GS} = 10 V (Note 4, 5)	--	80	--	nC
Q_{gs}	Gate-Source Charge		--	12	--	nC
Q_{gd}	Gate-Drain Charge		--	38	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	9	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	36	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 9 A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 9 A,	--	533	--	ns
Q_{rr}	Reverse Recovery Charge	dI_F / dt = 100 A/us (Note 4)	--	6.2	--	uC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L =14.2 mH, VDD = 50V, RG = 25Ω, Starting TJ = 25°C
3. I_{SD}≤9A, di/dt ≤200A/us, VDD ≤ BVDSS, Starting TJ = 25°C
4. Pulse Test : Pulse width ≤ 300us, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

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Typical Characteristics

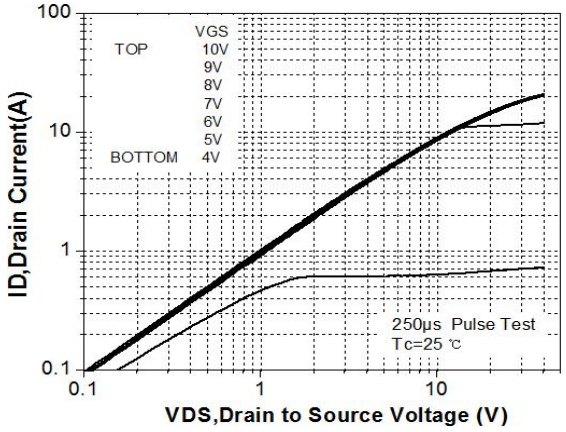

Figure 1. On-Region Characteristics

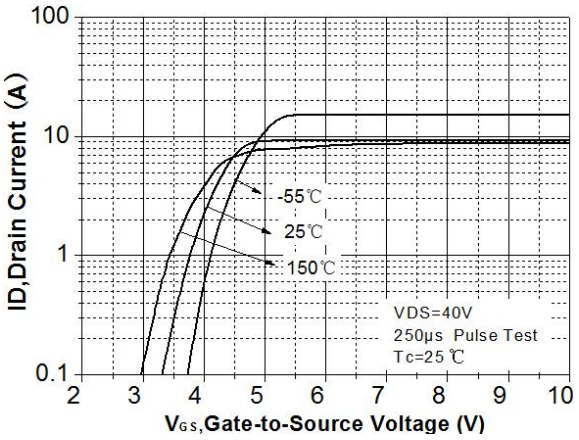

Figure 2. Transfer Characteristics

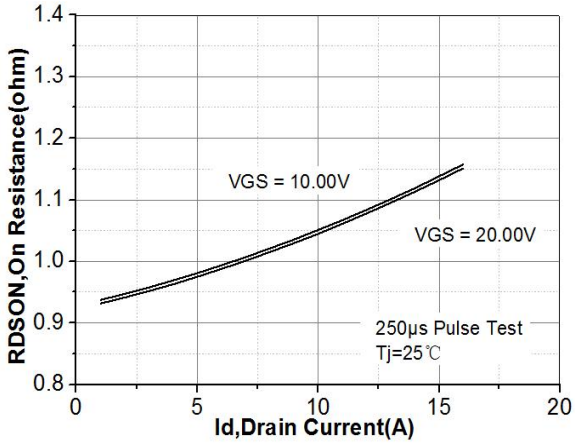

Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

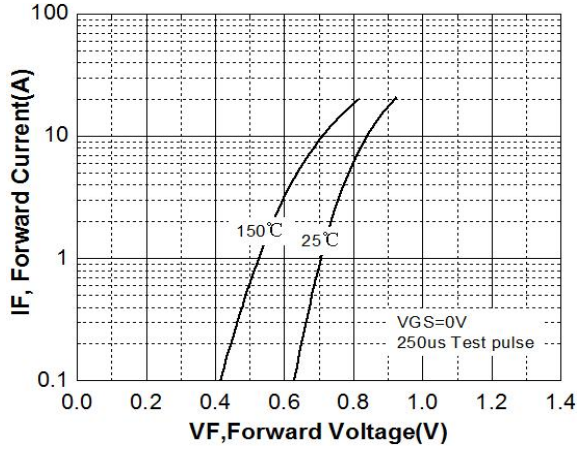

Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

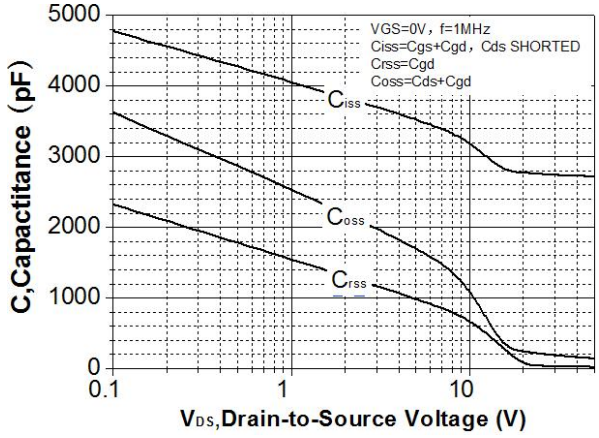

Figure 5. Capacitance Characteristics

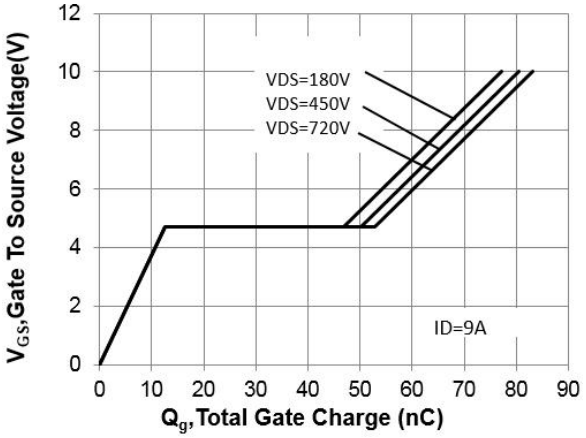

Figure 6. Gate Charge Characteristics

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Typical Characteristics (Continued)

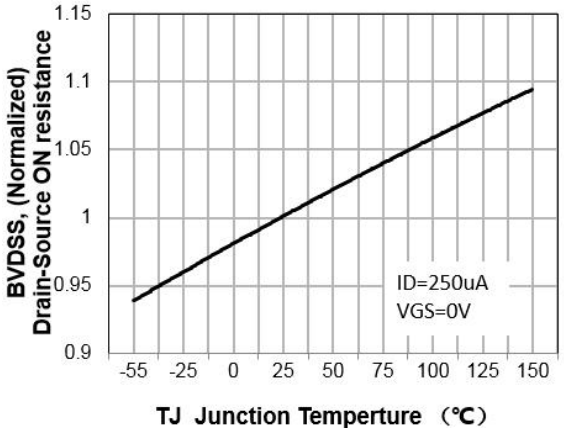

Figure 7. Breakdown Voltage Variation vs Temperature

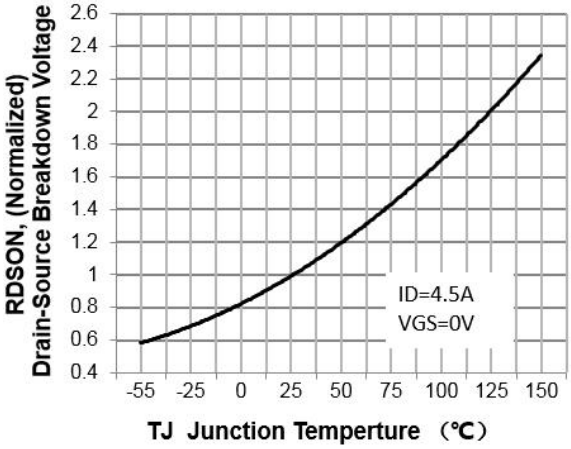

Figure 8. On-Resistance Variation vs Temperature

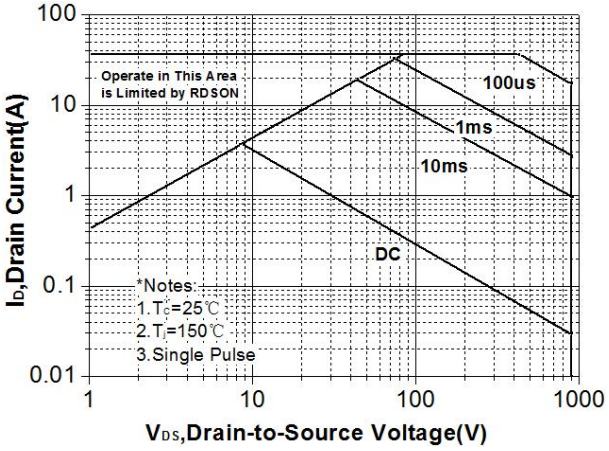

Figure 9. Maximum Safe Operating Area

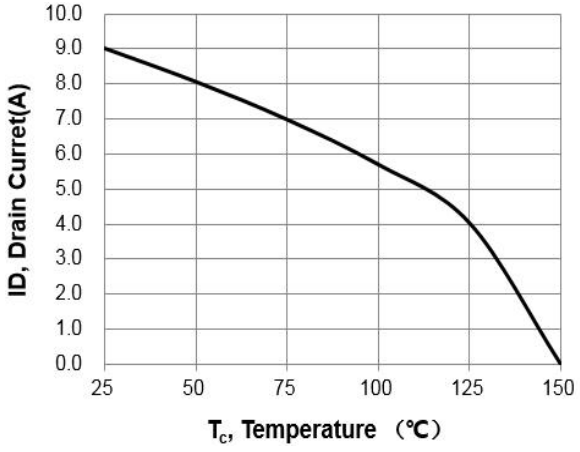

Figure 10. Maximum Drain Current vs Case Temperature

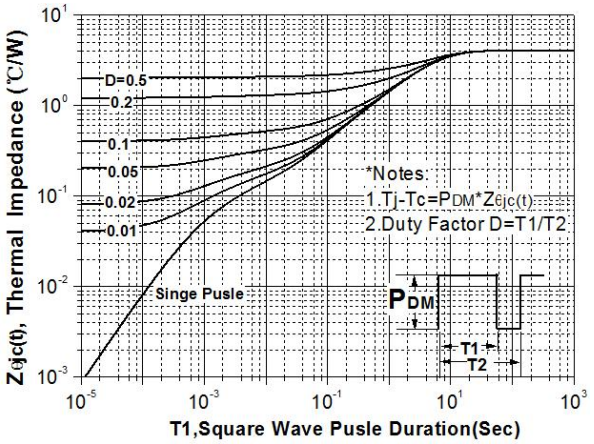

Figure 11. Transient Thermal Response Curve

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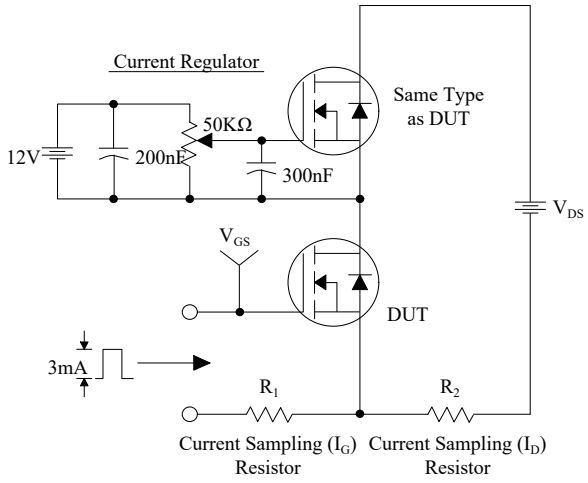
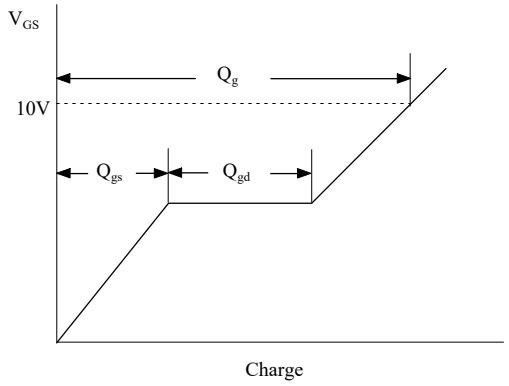
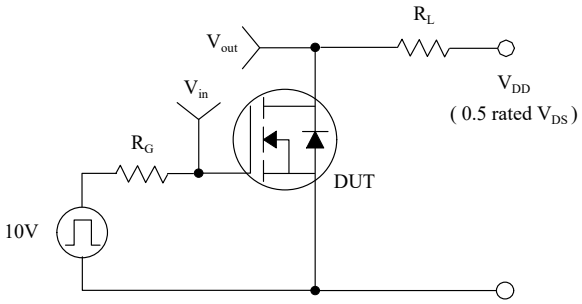
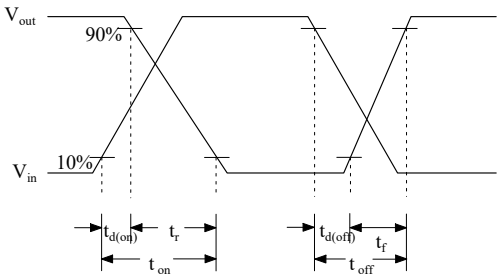
Gate Charge Test Circuit & Waveform



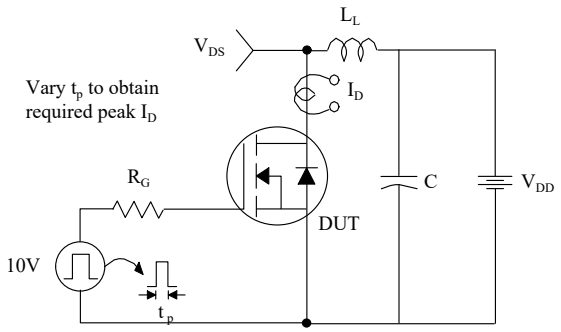


Resistive Switching Test Circuit & Waveforms

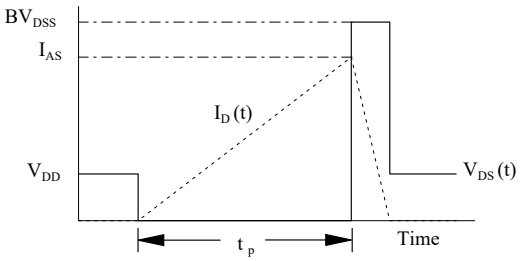




Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L_L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



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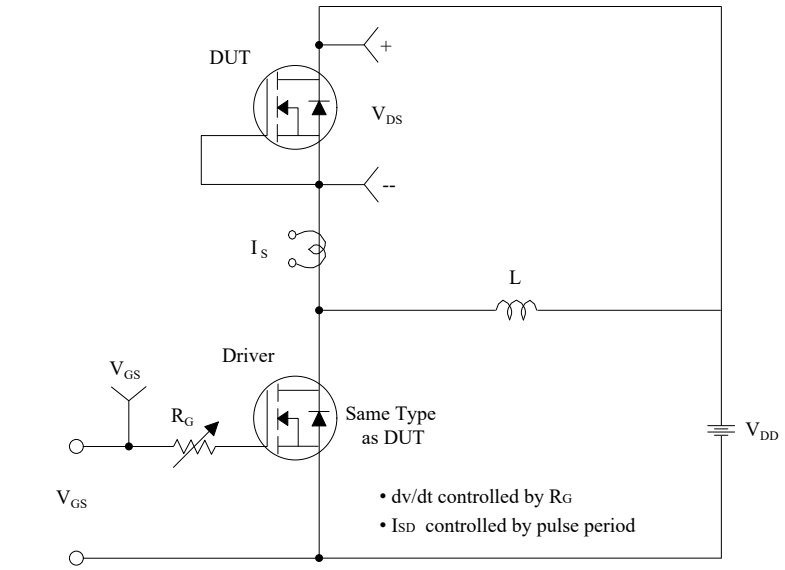
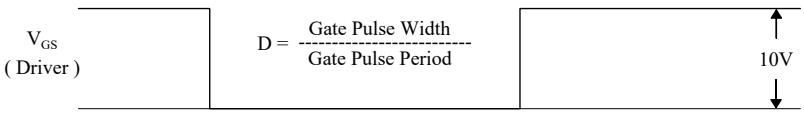
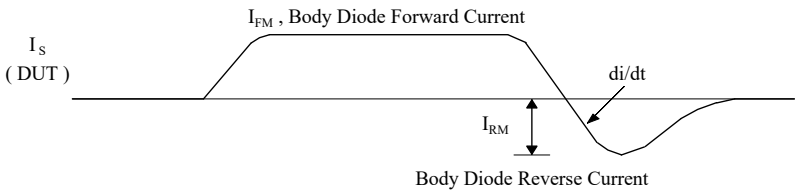
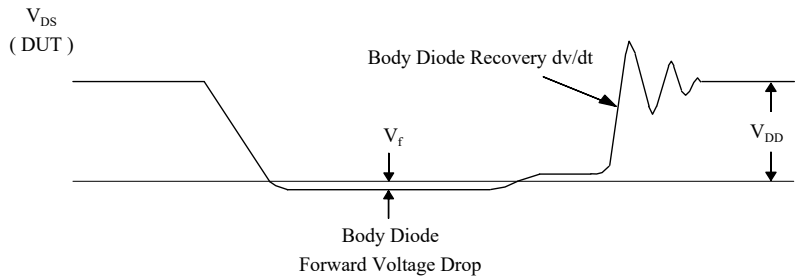
Peak Diode Recovery dv/dt Test Circuit & Waveforms









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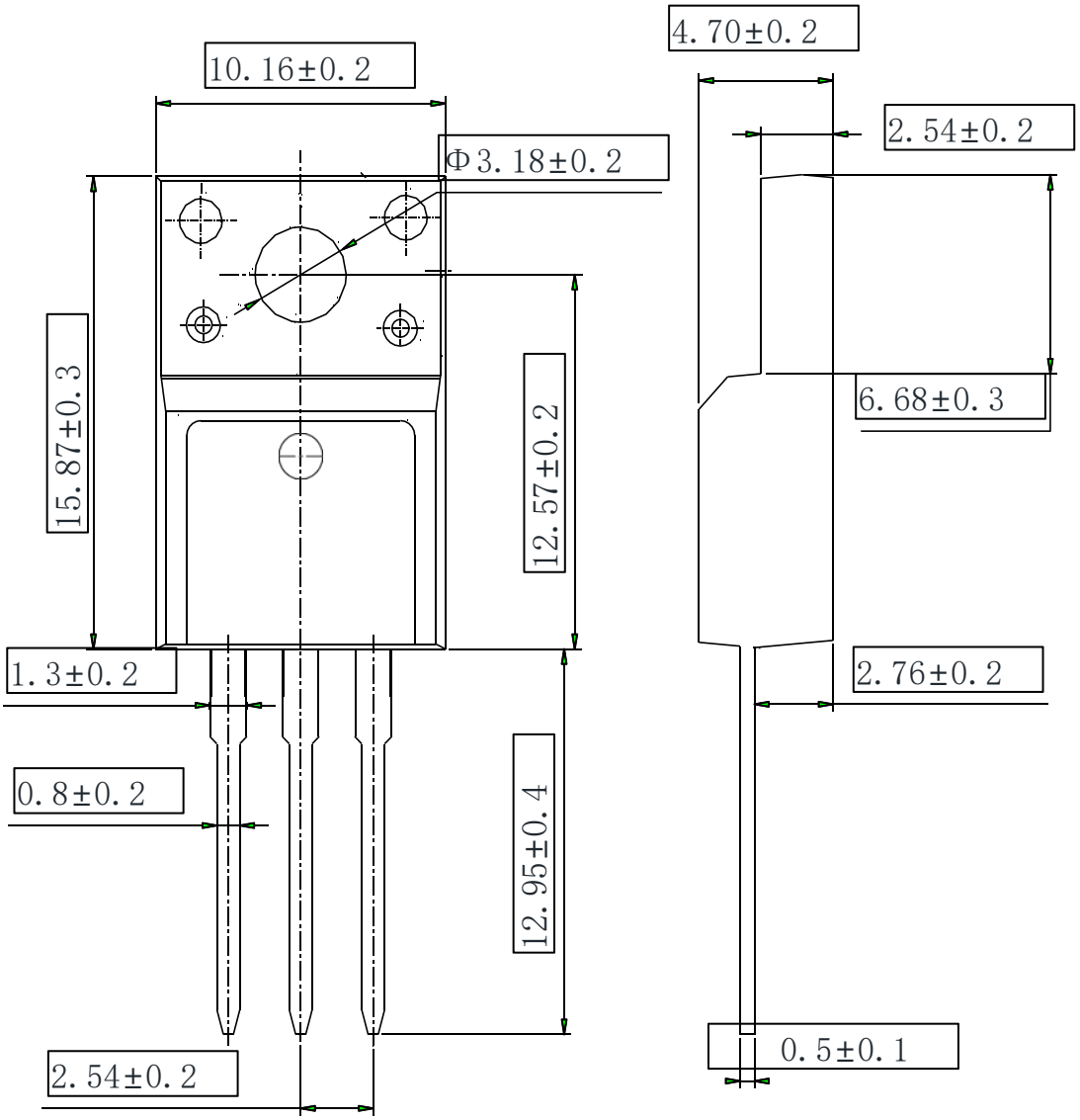
TO-220F OUTLINE



NOTE：
1The plastic package is not marked as smooth surfaceRa=0.1;Subglossy surfaceRa=0.8
2.Undeclared tolerance±0.15,Unmarked filletRmax=0.25

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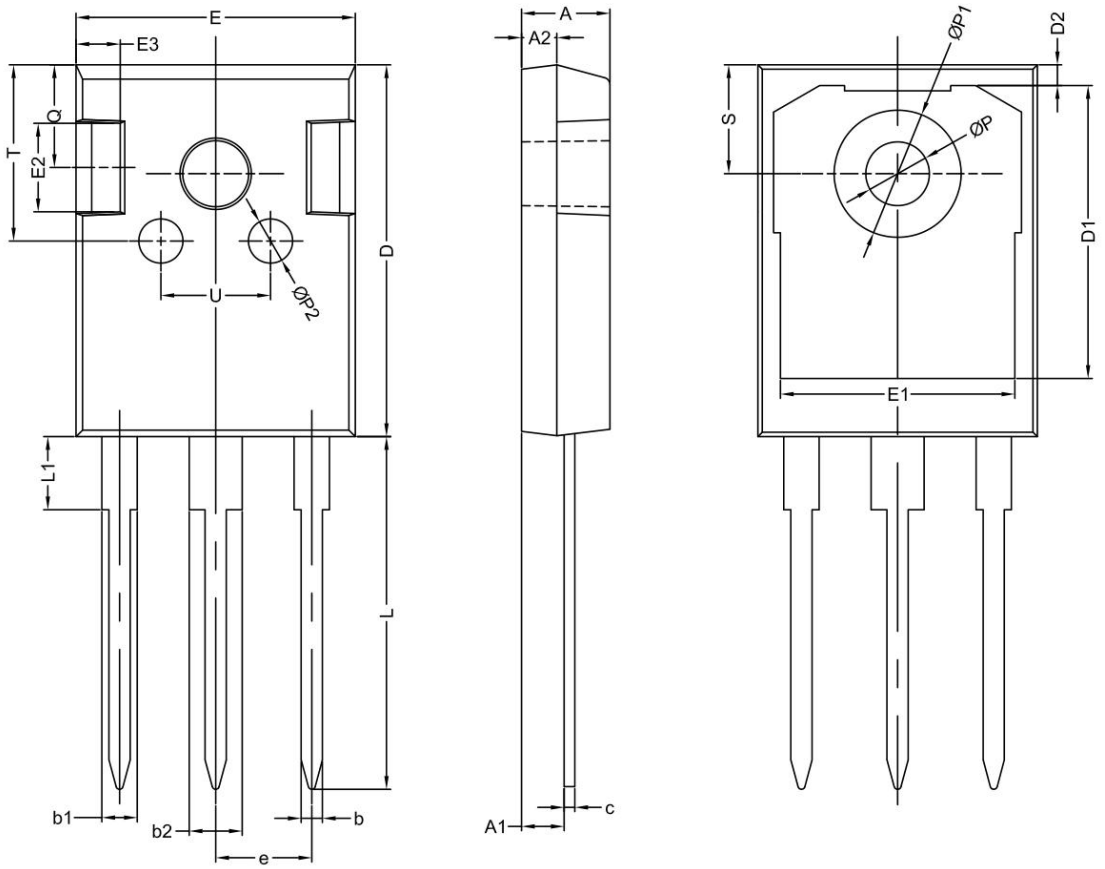

SYMBOL	Mechanical Dimensions/mm			SYMBOL	Mechanical Dimensions/mm			SYMBOL	Mechanical Dimensions/mm		
	MIN	NOM	MAX						MIN	NOM	MAX
A	4.80	5.00	5.20	D	20.80	21.00	21.20	L1	-	4.13	-
A1	2.21	2.41	2.61	D1	-	16.55	-	⌀ P	3.5	3.6	3.7
A2	1.90	2.00	2.10	E	15.60	15.80	16.0	⌀ P1	-	-	7.40
b	1.10	1.20	1.35	E1		13.3		⌀ P2	-	2.50	-
b1	-	2.00	-	E2		5.0		Q	-	5.8	-
b2	-	3.00	-	e		5.44		S	6.05	6.15	6.25
c	0.55	0.60	0.75	L	19.42	19.92	20.42	T	-	10.0	-

NOTE:
1The plastic package is not marked as smooth surfaceRa=0.1;Subglossy surfaceR
a=0.8
2.Undeclared tolerance±0.15,Unmarked filletRmax=0.25

NAME	TO-247 OUTLINE	UNIT	mm	DESIGNED	Shawn	THIRD ANGLE SYSTEM
DWGNO		PAGE	1 OF 1	CHECKED		
VERSION	Ver1.0	ISSUE DATE		APPROVED		

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